

1. Record Nr.	UNINA9911019569503321
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Titolo	Nanodevices for Integrated Circuit Design
Pubbl/distr/stampa	Newark : , : John Wiley & Sons, Incorporated, , 2023 ©2023
ISBN	9781394186389 139418638X 9781394186396 1394186398
Edizione	[1st ed.]
Descrizione fisica	1 online resource (304 pages)
Altri autori (Persone)	KumarAbhishek Srinivasa RauK MudimelaPrasantha R
Soggetti	Nanotechnology Integrated circuits
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
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Sommario/riassunto

This book, 'Nanodevices for Integrated Circuit Design', provides a comprehensive exploration of advanced nanotechnologies and their applications in integrated circuit design. Edited by experts Suman Lata Tripathi, Abhishek Kumar, K. Srinivasa Rao, and Prasantha R. Mudimela, it delves into topics such as nanowire field-effect transistors, silicon nanowire devices, and molybdenum disulfide FETs. The book also covers the kink effect in transistors, next-generation quantum well devices, and the role of FinFETs as biosensors. It aims to address the challenges in fabricating and utilizing nanodevices, with discussions on

RF analysis, biodegradable electronics, and edge AI technology. Intended for researchers, professionals, and students in the fields of electronics and nanotechnology, this work offers insights into the latest advancements and methodologies in the design and application of nanodevices.
